

IT/and KI heating said semiconductor film and said metal to crystallize said semiconductor film; and
forming a channel region,
wherein said channel region is formed of the crystallized semiconductor film.

REMARKS

At the outset, the Examiner is thanked for the review and consideration of the present application.

The Examiner's Final Office Action dated May 9, 2001, has been received and its contents reviewed. Claims 60-62, 72-74, 81 and 83-84 are ^{for review} pending in the present application, as claims 19-59, 63-71, 75-80, and 82 have been withdrawn from further consideration pursuant to 37 CFR 1.142(b) as being drawn to non-elected species. Of the remaining pending claims, claims 60 and 72 are independent.

Referring now to the Office Action, claims 60-62, 72-74, 81 and 83-84 are rejected under 35 U.S.C. §112, second paragraph, as allegedly being indefinite for failing to particularly point out and distinctly claim the subject matter which Applicants' regard as their invention. The Examiner contended that the metes and bound of oxygen and/or hydrogen concentration in the silicon nitride film are unclear, and that Applicants have consistently failed to properly address this issue. Applicants respectfully direct the Examiner to the Amendment filed on October 20, 2000, particularly page 6, last paragraph where a response was provided with respect to the §112, second paragraph, rejection. As previously submitted, the rejection is improper for the reason that there is no basis in §112, second paragraph, that a claimed invention must distinguish over a prior art. Accordingly, Applicants respectfully request reconsideration and withdrawal of the §112, second paragraph, rejection.

Claim 84 is rejected under 35 U.S.C. §102(a) as allegedly being anticipated by JP 6-267978 in view of Wolf, and as being generic. It is noted that Wolf is cited only as a teaching reference and not as a secondary reference.

As amended, claim 84 further recites forming a channel region, wherein the channel region is formed of the crystallized semiconductor film. Applicants respectfully submit that

while the channel region of the presently claimed invention is crystallized, a channel region disclosed in the JP 6-267978 cited by the Examiner is amorphous. Furthermore, as amended, claim 84 is not generic.

The Court of Appeals for the Federal Circuit has consistently held that "Anticipation requires the presence in a single prior art reference disclosure of each and every element of the claimed invention, arranged as in the claim." Lindemann Maschinenfabrik GmbH v. American Hoist & Derrick, 221 USPQ 481, 485 (Fed. Cir. 1984). JP 6-267978 clearly fails to disclose features positively recited and claimed in applicants' independent claim 84. More particularly, JP 6-267978 fails to disclose forming a channel region, wherein said channel region is formed of the crystallized semiconductor film. Accordingly, JP 6-267978 does not anticipate claim 84, and the rejection of claim 84 is respectfully requested to be reconsidered and withdrawn.

Claims 60-62, 72-74, 81 and 83-84 are rejected under the judicially created doctrine of obviousness-type double patenting as being unpatentable over claims 1-12 of U.S. Patent No. 5,643,826 in view of JP 6-267978. Applicants respectfully request that the rejection be held in abeyance until the claims are allowable.

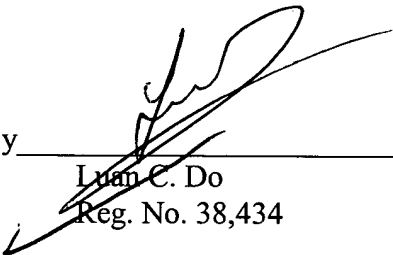
With respect to the non-elected claims, Applicants respectfully submit that the non-elected claims should be allowable in the event that amended claim 84 becomes allowable.

For the foregoing amendment and arguments, the above rejections are respectfully traversed and requested to be reconsidered and withdrawn.

CONCLUSION

Having responded to all rejections set forth in the outstanding Final Office Action, it is submitted that claims 60-63, 72-74, 81 and 83-84 are now in condition for allowance. An early and favorable Notice of Allowance is respectfully solicited. In the event that the Examiner is of the opinion that a brief telephone or personal interview will facilitate allowance of one or more of the above claims, the Examiner is courteously requested to contact Applicants' undersigned representative.

Respectfully submitted,

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VERSIONS OF AMENDED CLAIMS
WITH MARKINGS TO SHOW CHANGES MADE

84. (Amended) A method of manufacturing a semiconductor device comprising the steps of:
- forming a silicon nitride film containing at least one of hydrogen and oxygen over a substrate;
 - depositing a semiconductor film comprising amorphous silicon on said silicon nitride film;
 - disposing a metal contact with at least a selected portion of said semiconductor film; [and]
 - heating said semiconductor film and said metal to crystallize said semiconductor film; and
 - forming a channel region,
 - wherein said channel region is formed of the crystallized semiconductor film.